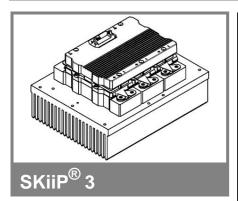
## SKiiP 513GD122-3DUL



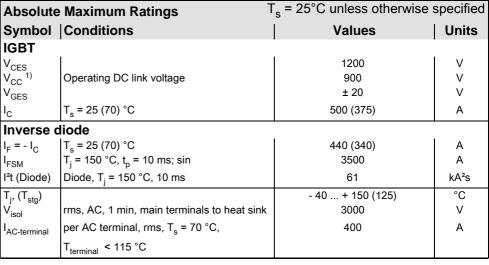
## 6-pack-integrated intelligent Power System

### **Power section** SKiiP 513GD122-3DUL

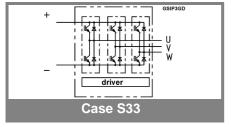
Data

#### **Power section features**

- SKiiP technology inside
- SPT (Soft Punch Through) IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- 1) with assembly of suitable MKP capacitor per terminal



Characteristics			$T_s$ = 25 °C unless otherwise specified						
Symbol	Symbol  Conditions				min.	typ.	max.	Units	
<b>IGBT</b>									
V <sub>CEsat</sub>	I <sub>C</sub> = 300 A, measured at te	T <sub>j</sub> = 25 (1 erminal	25) °C;			2,3 (2,5)	2,6	V	
$V_{CEO}$	$T_i = 25 (12)$	5) °C; at te	erminal			1,1 (1)	1,3 (1,2)	V	
$r_{CE}$	$T_{j} = 25 (12)$					3,8 (5)	4,5 (5,6)	mΩ	
I <sub>CES</sub>	$V_{GE} = 0 \text{ V},$ $T_i = 25 (12)$	V <sub>CE</sub> = V <sub>CI</sub> 5) °C	ES,			1,2 (36)		mA	
$E_{on} + E_{off}$	$I_{\rm C}^{\rm J}$ = 300 A,		0 V			90		mJ	
	$T_{j} = 125  ^{\circ}C$	s, V <sub>CC</sub> = 90	00 V			159		mJ	
R <sub>CC+EE</sub>	terminal ch	ip, T <sub>j</sub> = 25	S°C			0,5		mΩ	
$L_{CE}$	top, bottom	1				12		nH	
C <sub>CHC</sub>	per phase,	AC-side				1,7		nF	
Inverse o									
$V_F = V_{EC}$	I <sub>F</sub> = 300 A, measured at te	T <sub>j</sub> = 25 (1 erminal	25) °C			1,8 (1,5)	2,3	V	
V <sub>TO</sub>	T; = 25 (12	5) °C				1 (0,7)	1,2 (0,9)	V	
r <sub>T</sub>	$T_j = 25 (12)$ $T_j = 25 (12)$	5) °C				2,6 (2,8)	3,5 (3,7)	mΩ	
E <sub>rr</sub>	$I_{\rm C} = 300  \text{A},$	$V_{CC} = 60$	0 V			24		mJ	
	T <sub>j</sub> = 125 °C	s, V <sub>CC</sub> = 90	V 00			31		mJ	
Mechani	cal data								
$M_{dc}$	DC termina	ıls, SI Uni	ts		6		8	Nm	
$M_{ac}$	AC termina	-			13		15	Nm	
W	SKiiP® 3 S	SKiiP® 3 System w/o heat sink				2,4		kg	
W	heat sink	heat sink				7,5			
Thermal characteristics (PX16 heat sink with fan SKF16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc.IEC 60747-15)									
R <sub>th(j-s)I</sub>	per IGBT						0,059	K/W	
R <sub>th(j-s)D</sub>	per diode						0,115	K/W	
Z <sub>th</sub>	R <sub>i</sub> (mK/W)	R <sub>i</sub> (mK/W) (max. values)				tau <sub>i</sub> (s)			
	1	2	3	4	1	2	3	4	
$Z_{th(j-r)I}$	10,2	28,8	21	0	363	0,18	0,04	1	
$Z_{\text{th(j-r)D}}$	36	36	54	60	30	5	0,25	0,04	



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1,4

210

85

11

0,4

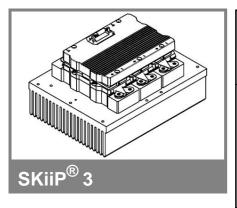
20

5,5

 $Z_{th(r-\underline{a})}$ 

2,1

# SKiiP 513GD122-3DUL



# 6-pack-integrated intelligent Power System

6-pack integrated gate driver SKiiP 513GD122-3DUL

Data

#### **Gate driver features**

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- · Interlock of top/bottom switch
- Isolation by transformer
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings T	T <sub>a</sub> = 25 °C unless otherwise specified		
Symbol	Conditions	Values	Units	
$V_{S2}$	unstabilized 24 V power supply	30	V	
$V_{i}$	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
$V_{isollO}$	input / output (AC, rms, 2 s)	3000	V	
V <sub>isoIPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> ≤ 10 pC;	1170	V	
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2 s)	1500	V	
f <sub>sw</sub>	switching frequency	15	kHz	
f <sub>out</sub>	output frequency for I <sub>peak(1)</sub> =I <sub>C</sub>	15	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 <b>+</b> 85	°C	

Characte	eristics	(T <sub>a</sub>			= 25 °C)
Symbol	Conditions	min.	typ.	max.	Units
$V_{S2}$	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 24 V	365+30*f/kHz+0,00111*(I <sub>AC</sub> /A) <sup>2</sup>			mA
V <sub>iT+</sub>	input threshold voltage (High)			12,3	V
$V_{iT-}$	input threshold voltage (Low)	4,6			V
R <sub>IN</sub>	input resistance		10		kΩ
C <sub>IN</sub>	input capacitance		1		nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,3		μs
$t_{d(off)IO}$	input-output turn-off propagation time		1,3		μs
tpERRRESET	error memory reset time		9		μs
$t_{TD}$	top / bottom switch interlock time		3		μs
I <sub>analogOUT</sub>	max. 5 mA; 8 V corresponds to 15 V supply voltage for external components		500		Α
I <sub>s1out</sub>	max. load current			50	mA
I <sub>TRIPSC</sub>	over current trip level (I <sub>analog</sub> OUT = 10 V)		625		Α
$T_tp$	over temperature protection	110		120	°C
UDCTRIP	U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V); (option for GB types)		900		V

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